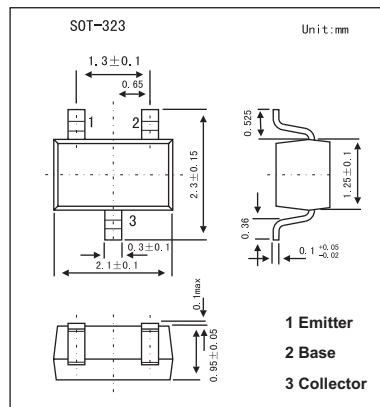


■ Features

- Small dimension
- High DC current gain



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	120	V
Collector-emitter voltage	V _{CEO}	120	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	50	mA
Total power dissipation	P _T	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 120V, I _E =0			0.05	μA
Emitter cutoff current	I _{EB0}	V _{EB} = 5V, I _C =0			0.05	μA
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 1mA*	135	600	900	
		V _{CE} = 6V, I _C = 0.1mA	100	580		
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = 10mA, I _B = 1mA		0.07	0.3	V
Base-emitter voltage *	V _{BE}	V _{CE} = 6V, I _C = 1mA	0.55	0.59	0.65	V
Gain bandwidth product	f _T	V _{CE} = 6V, I _E = -1mA	50	110		MHz
Output capacitance	C _{ob}	V _{CB} = 30V, I _E = 0, f = 1.0MHz		1.6	2.5	pF

* Pulse test: tp ≤ 350 μs; d ≤ 0.02.

■ hFE Classification

Marking	D15	D16	D17	D18
hFE	135~270	200~400	300~600	450~900